



2812

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#6/a

Applicant : Been-Yih Jin et al.
Serial No. : 10/081,992
Filed : February 21, 2002
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Art Unit : 2812
Examiner : Ron E. Pompey
Confirmation No.: 1734

3/6/3

Smile

Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

In response to the Office Action dated November 21, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 8, 16, and 19 as follows:

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-- 8. (Amended) A transistor comprising:

a semiconductor substrate, the substrate being substantially free of silicon; and

a gate dielectric layer formed over a portion of the substrate, wherein the gate dielectric comprises a material having a dielectric constant greater than about 10.

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

Date of Deposit February 21, 2003
Signature *Melissa K. Addis*

Melissa K. Addis
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